

Figure 1. (a)-(c) Bright field and (d)-(f) High Resolution Transmission Electron Microscopy data for a 12 nm *as-deposited* HfO₂ film from TEMAHf and H₂O at 250°C on native oxide GaAs(100) surfaces. The presence of crystallites is evident in all images. Some of the grains span the film thickness but many smaller ones are clearly visible. The film has not been subjected to post deposition thermal treatment.



Figure 2. (a)-(f)) High Resolution Transmission Electron Microscopy data for a 6 nm HfO₂ film deposited from TEMAHf and H₂O at 250°C on 4.6 nm chemical oxide GaAs(100) surfaces. The presence of crystallites is evident in all images. The film has not been subjected to post deposition thermal treatment.